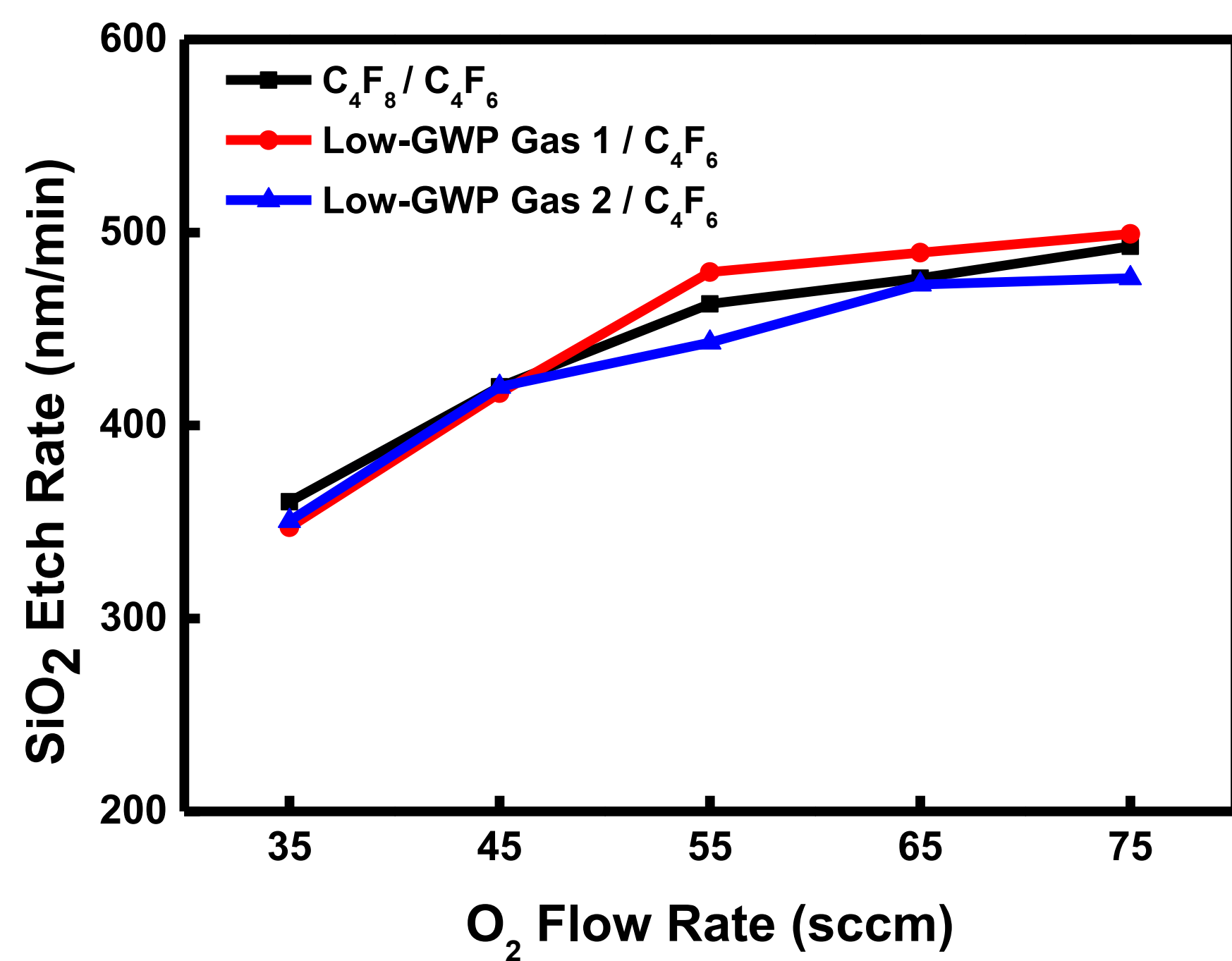


(a)



(b)

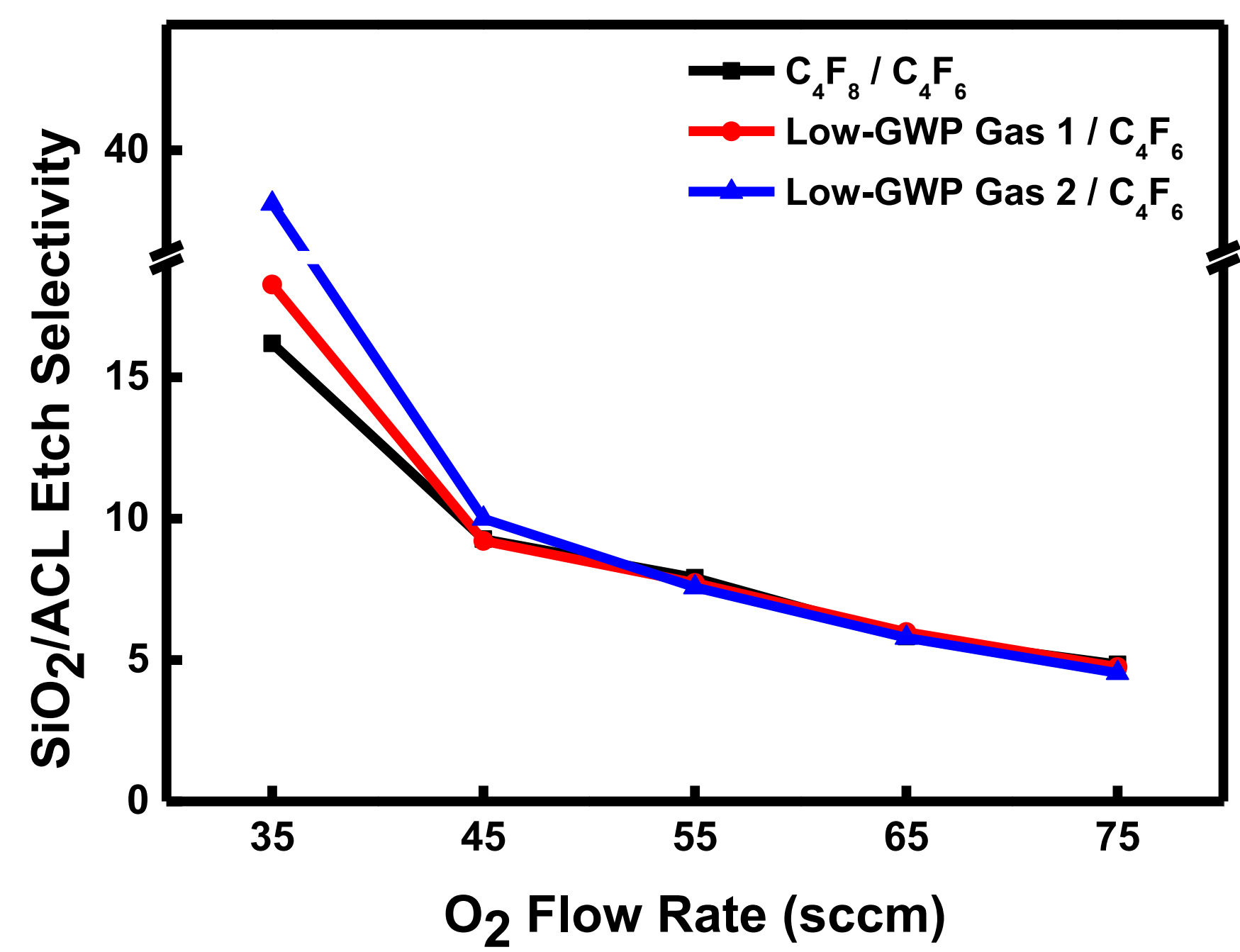
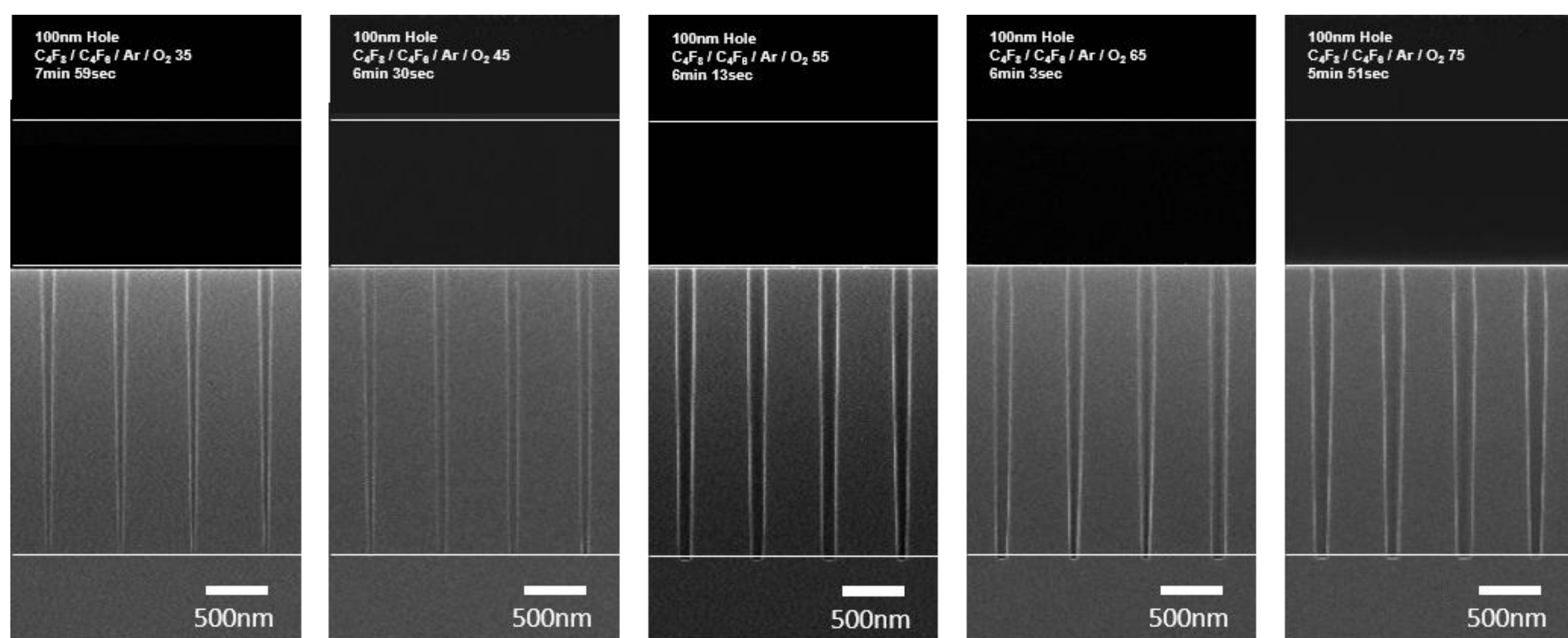
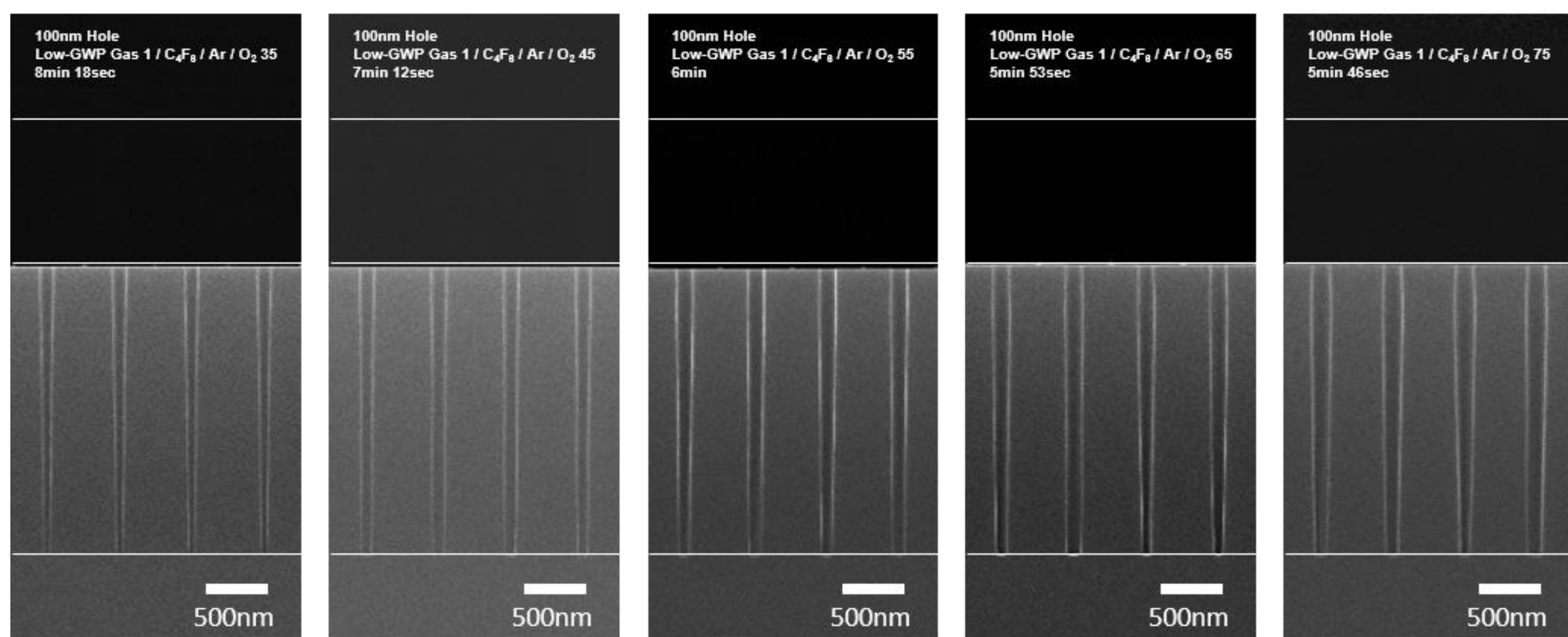


Figure1. (a) SiO₂ etch rate and (b) SiO₂/ACL etch selectivity as a function of O₂ flow rate (35-75 sccm) for C₄F₈/C₄F₆/Ar/O₂, Low-GWP Gas 1/C₄F₆/Ar/O₂, Low-GWP Gas 2/C₄F₆/Ar/O₂. Other process conditions were kept constant across the three gas chemistries.

(a)



(b)



(c)

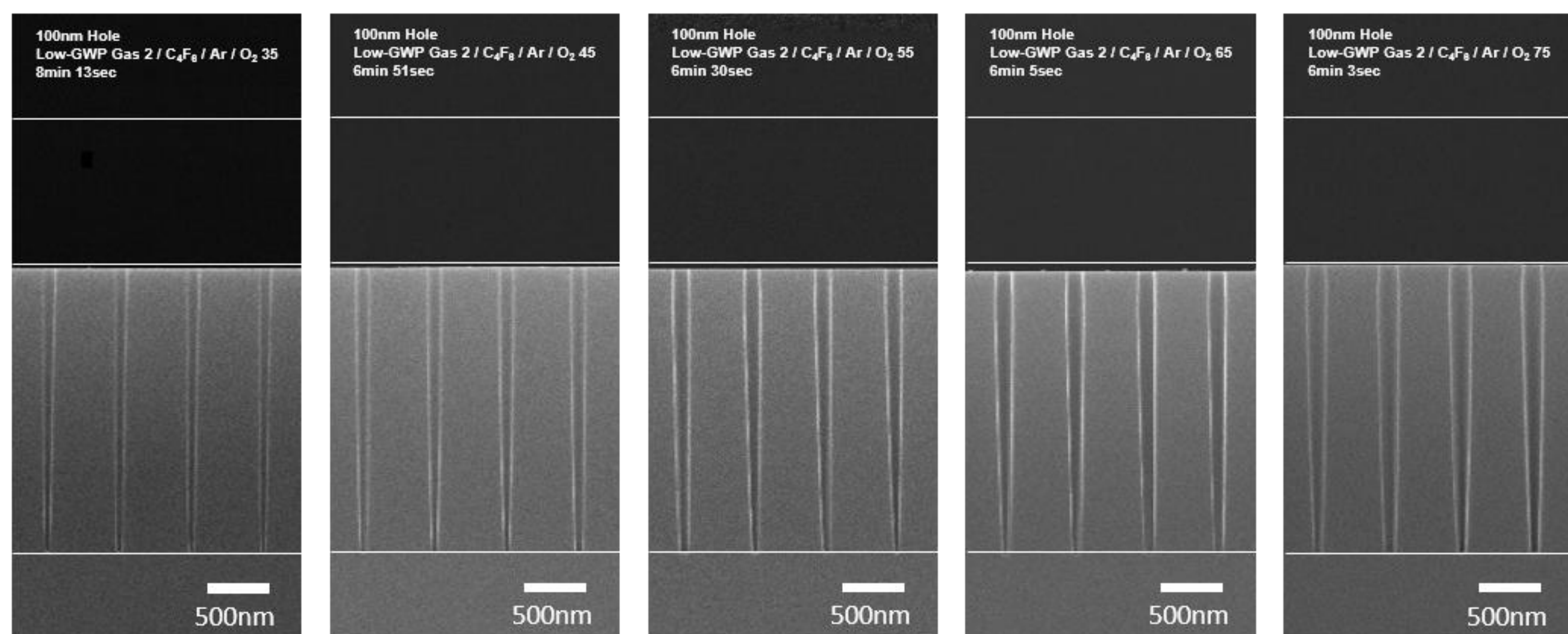


Figure2. Cross-sectional FE-SEM overetch profiles of SiO₂ 100nm hole patterns as a function of O₂ flow rate for (a) C₄F₈, (b) Low-GWP Gas 1, and (c) Low-GWP Gas 2. 2.4 μm-thick SiO₂ holes were etched with 20% overetch, with etch time for each condition determined from the etch data in Figure 1. The ACL mask was removed by O₂ plasma ashing.